



A Couple Of Considerations on the Dynamics of Defectivity **Generation in CMP Technology**

Yehiel Gotkis







Maskless Nanowriter HR001-06-03-0008





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- Post- CMP Defectivity is one of the major factors affecting its performance (&FAB yield), and scratching is its most problematic constituent.
- Cu is a very soft material, thereby for Cu CMP scratching is especially painful

Identification of scratching mechanism, origin and source of scratching objects is vitally critical both in R&D (process & consumables) and production environments (process control & troubleshooting).



Compensating pad conditioning action is a MUST in CMP



Accelerating Yie

A two-object, wafer&pad, interactive system, with one of them, the wafer, purposely changing its state, in principle, is unstable.

A third object, pad conditioning unit, compensating for drifts in wafer/pad contact interface, is introduced to manage stability.





Pad Conditioning (PC)

- It is a combo of abrasive and chemical action applied to the pad surface.
- Its purpose clean the existing pores and open new ones, remove by-products and upper glazed material.
 - Only balanced PC, exactly compensating for the wafer/pad interaction effects, provides both quality and stability.
- Too mild PC action does not compensate well, overconditioning causes numerous quality issues.



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The most frequently used CMP model is oversimplified and, thereby, misleading



Wafer and pad interact via protrusion/intrusion engagement of fine features, asperities, and this is the key coupling phenomenon, which has always to be kept in mind, while discussing any CMP problem (SHR, PL, D&E, defectivity, selectivity etc.)

The more intrusive and aggressive the asperities the stronger their impact on CMP performance

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Wafer Acually Engages With The Interfacial Skin Layer, Asperities And Debris...



...and not with bulk polymer!





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Three types of interactions in a system of two_surfaces & a_ball



- 1. Hard object (HO) trapped in a deep surface defect (d > r_{HO}) One translational degree of freedom (ODOF) \rightarrow scratching
- 2. HO trapped in a shallow (d < r_{HO}) surface defect (capable to roll out) Two degrees of freedom, namely, translation and rolling (TDOF) \rightarrow HO pattern printing. "Rolling stones"
- 3. HO trapped by defects in both surfaces Zero degrees of freedom (ZDOF)→ damage due to stress accumulation until one of the defects or the HO is destroyed or strongly deformed.



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7 4/5/2007

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Analyze the details of the particle trajectories in the bubble-chamber analysis fashion









"Chatter" marks It looks like the "chatter" marks indeed are periodic Chatter mark- a mark left on something that barg hrating to machined, caused by vibration during the machining process. Large rough particle, Chatter mark- (YG) periodic deformation marks produced as

a result of "Stick-and-Slip" translation









An early published case of "rolling stones"



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Particle erosion/distortion during rolling





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RS profile



- Shaped like a rough base ball (λ/w ≈1.5 3)
 - Sized 1-10 microns
 - Hard enough to leave prints on copper, but relatively soft not to damage significantly hard dielectrics (silica).
 - Compressed/eroded/deformed, but preserves its integrity while being rolled between the pad and the wafer
 - Pops up suddenly, and suddenly disappears
 - Causes "shallow" (width>>depth), and frequently bundle scratching in ODOF cases

Now, when we've profiled the bad guys let's consider where they can arrive from









Back

RS candidates: 1. Slurry aggregates



- It requires ~10⁶ slurry abrasive particles to build a 5 µm aggregate, which is not likely to happen in short period of time between filtering point and point of use.
- Aggregates have loose structure and it is hard to believe they can withstand high polishing pressure and friction and preserve their structural integrity, as RS do.

Slurry aggregates are not the likely candidates for the RS role



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RS candidates: 2. Cu grains



- Cu grains are known to be pulled sometimes out.
- However, the CuDD grains hardly get bigger than 1-2 μm

Cu grains also do not fit the RS profile





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...and they do get this capability while being impregnated with process components



- Fractured and cracked PCD species are easily impregnated with precipitated slurry agglomerates and process by-products, which converts them into reasonably hard and rough species capable to abrade and imprint.
- In the same time PCD particles still preserve significant portion of the polymer framework helping to keep their structural integrity while being rolled between the wafer and the pad.

PCD particles are excellent candidates for the RS role







RS candidates: **4. PC**_unit precipitation deposits



- PC_unit accumulates slurry precipitate over its surface and edge.
 - Getting thick precipitate cracks and delaminates, releasing large particles capable to scratch.

PC unit deposits are also very realistic potential sources of scratching particles







Scratches (ODOF and ZDOF cases)





ZDOF case- scratchier trapped by both upper and lower surface defects







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21 4/5/2007

Go to

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An important question at the end

Out of three major process steps, namely, BULK, SL and BARRIER&BUFF, which one is the most "scratch productive"?



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Considerations



I. Bulk

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- RR ~ 100 A/sec (6000 Å/min)
- scratch depth ~ 1000 Å
- It requires 10 sec to polish the scratch out.
- Scratch generation is not cumulative. Only the scratches generated at the last 10 seconds of the BULK step are transferred to the SL step, at which, however, they will be anywhere removed.

Scratching generated during the BULK step <u>would not</u> be a very endangering matter,

lf...



... if early BULK scratches were entirely harmless



And they are not!







Considerations



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- The heterogeneous surface appears first, and the secondary topography (recess SH) starts to develop at SL.
- Also, scratches induced at this phase, will have little chance to be removed at the next step, <u>especially if high</u> <u>selectivity BARRIER process is used.</u>
- However, everything is mild at SL (DF, amount of

material to be removed, RR, pad load etc.), so scratch generation efficiency (frequency, depth, length) is significantly lower and the scratches are much shallower than the BULK ones.

Soft Landing --- Mild (if any) Scratching

25 4/5/2007



Considerations





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Summary



- By analyzing details of scratch structure, one can learn a lot about the scratching mechanism, root cause and possible problem solution.
- Pad conditioning debris and conditioning unit deposits should be seriously considered while dealing with scratching issues
- PC action is critical at each process step and has to be finely tuned to the lowest possible aggressiveness.
- Although BULK scratches are normally wiped out, they may leave behind lined up sequences of stress induced corrosion spots.
- Barrier&Buff potentially are the most scratch-productive steps, thereby PC action at this phase has to be as delicate as possible (and also preferentially ex situ).





Thank you for your attention!

EE 298-12 State Technology and Devices Seminar

http://microlab.berkeley.edu/text/298-12.seminar

Friday, 23 March 2007 1-2 pm in the Hogan Room (521 Cory)

Dynamics Of Defect Generation

In CMP Technology

Dr. Yehiel Gotkis KLA-Tencor Corp. San Jose, CA

Abstract and slides available at

http://microlab.berkeley.edu/text/298-12.seminar

http://microlab.berkeley.edu/text/seminars/2007slides.html



Sliding on the heterogeneous CuDD surface...





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